

NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE2312 uses advanced trench technology to provide excellent $R_{\text{DS}(\text{ON})}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a battery protection or in other switching application.

General Features

• $V_{DS} = 20V, I_D = 4.5A$

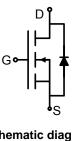
 $R_{DS(ON)}$ < 40m Ω @ V_{GS} =2.5V

 $R_{DS(ON)}$ < 33m Ω @ V_{GS} =4.5V

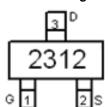
- High power and current handing capability
- Lead free product is acquired
- Surface mount package

Application

- Battery protection
- Load switch
- Power management



Schematic diagram



Marking and pin assignment



SOT-23 top view

Package Marking and Ordering Information

| Device Marking | Device | Device Package | Reel Size | Tape width | Quantity |
|----------------|---------|----------------|-----------|------------|------------|
| 2312 | NCE2312 | SOT-23 | Ø180mm | 8 mm | 3000 units |

Absolute Maximum Ratings (T₄=25 °C unless otherwise noted)

| 7 100 0 101 0 1 1 1 1 1 1 1 1 1 1 1 1 1 | | | | | |
|---|----------------------|------------------|------------------------|---|--|
| Paramete | Symbol | Limit | Unit | | |
| Drain-Source Voltage | V _{DS} | 20 | V | | |
| Gate-Source Voltage | V _G s | ±12 | V | | |
| Continuous Drain Correct | T _A =25℃ | | 4.5 | ۸ | |
| Continuous Drain Current | T _A =70°C | - I _D | 3.6 | A | |
| Drain Current-Pulsed (Note 1) | I _{DM} | 13.5 | Α | | |
| Maximum Power Dissipation | P _D | 1.25 | W | | |
| Operating Junction and Storage Temp | T_{J}, T_{STG} | -55 To 150 | $^{\circ}\!\mathbb{C}$ | | |

Thermal Characteristic

| Thermal Resistance, Junction-to-Ambient (Note 2) R _{0,JA} 100 °C/W | I nermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ | | |
|---|--|-----------------|--|--|
|---|--|-----------------|--|--|

Electrical Characteristics (T_A=25°C unless otherwise noted)

| Parameter | Symbol | Condition | Min | Тур | Max | Unit |
|--------------------------------|-------------------|---|-----|-----|-----|------|
| Off Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V I _D =250μA | 20 | 22 | - | V |



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| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =20V,V _{GS} =0V | - | - | 1 | μΑ |
|------------------------------------|---------------------|---|-----|------|------|----|
| Gate-Body Leakage Current | I _{GSS} | V _{GS} =±12V,V _{DS} =0V | - | - | ±100 | nA |
| On Characteristics (Note 3) | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | V _{DS} =V _{GS} ,I _D =250μA | 0.5 | 0.65 | 1.2 | V |
| Danier Course On Otata Basistan | R _{DS(ON)} | V _{GS} =2.5V, I _D =4.0 A | - | 21 | 40 | mΩ |
| Drain-Source On-State Resistance | | V _{GS} =4.5V, I _D =4.5A | - | 18 | 33 | mΩ |
| Forward Transconductance | g FS | V _{DS} =10V,I _D =4A | - | 10 | - | S |
| Dynamic Characteristics (Note4) | | | | • | | |
| Input Capacitance | C _{lss} |)/ O)/)/ O)/ | - | 500 | - | PF |
| Output Capacitance | Coss | $V_{DS}=8V,V_{GS}=0V,$ | - | 300 | - | PF |
| Reverse Transfer Capacitance | C _{rss} | F=1.0MHz | - | 140 | - | PF |
| Switching Characteristics (Note 4) | | | | • | | |
| Turn-on Delay Time | t _{d(on)} | | - | 20 | 40 | nS |
| Turn-on Rise Time | t _r | V _{DD} =10V,I _D =1A | - | 18 | 40 | nS |
| Turn-Off Delay Time | t _{d(off)} | V_{GS} =4.5 V , R_{GEN} =6 Ω | - | 60 | 108 | nS |
| Turn-Off Fall Time | t _f | | - | 28 | 56 | nS |
| Total Gate Charge | Qg | | - | 10 | 15 | nC |
| Gate-Source Charge | Q _{gs} | V _{DS} =10V,I _D =3A,V _{GS} =4.5V | - | 2.3 | - | nC |
| Gate-Drain Charge | Q_{gd} | | - | 2.9 | - | nC |
| Drain-Source Diode Characteristics | | • | | • | • | |
| Diode Forward Voltage (Note 3) | V _{SD} | V _{GS} =0V,I _S =1A | - | - | 1.2 | V |
| Diode Forward Current (Note 2) | Is | | - | - | 4.5 | Α |

Notes:

- **1.** Repetitive rating: pulse width limited by maximum junction temperature.
- **2.** Surface mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse test: pulse width \leq 300µs, duty cycle \leq 2%.
- 4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

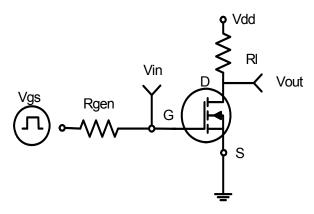


Figure 1:Switching Test Circuit

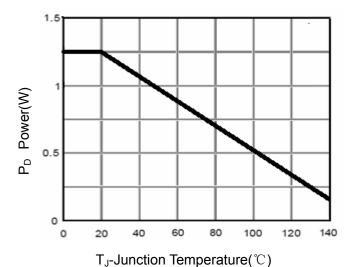


Figure 3 Power Dissipation

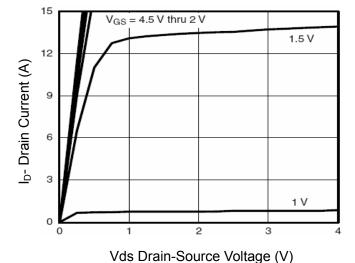


Figure 5 Output Characteristics

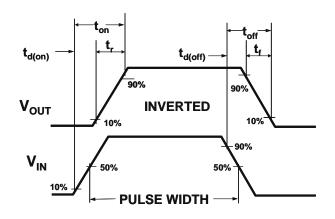


Figure 2:Switching Waveforms

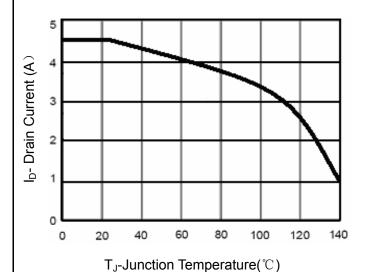


Figure 4 Drain Current

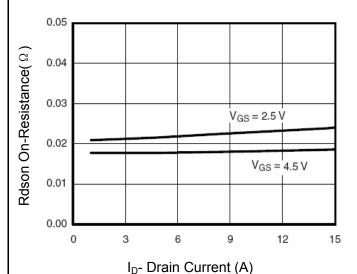
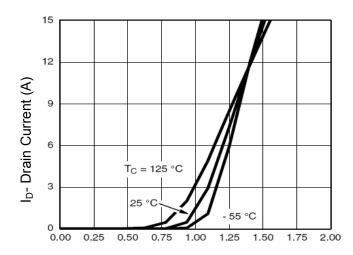


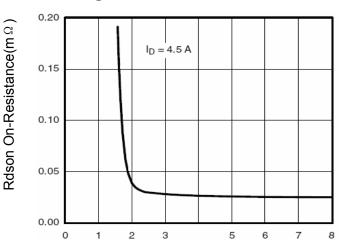
Figure 6 Drain-Source On-Resistance





Vgs Gate-Source Voltage (V)

Figure 7 Transfer Characteristics



Vgs Gate-Source Voltage (V)

Figure 9 Rdson vs. Vgs

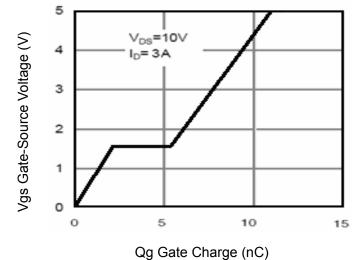


Figure 11 Gate Charge

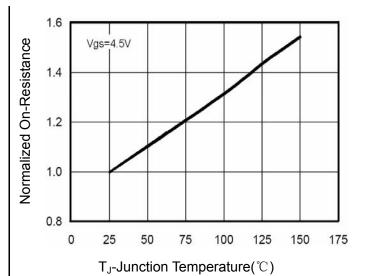
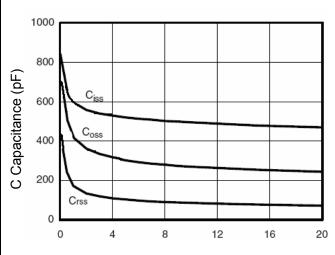
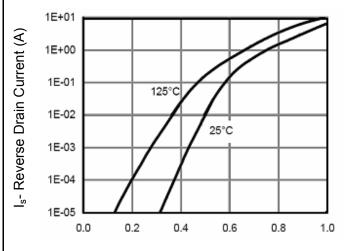


Figure 8 Drain-Source On-Resistance



Vds Drain-Source Voltage (V)

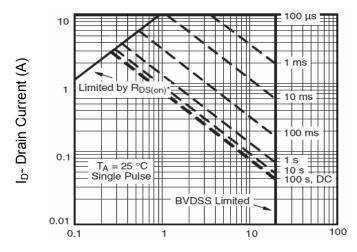
Figure 10 Capacitance vs Vds



Vsd Source-Drain Voltage (V)

Figure 12 Source- Drain Diode Forward





Vds Drain-Source Voltage (V)

Figure 13 Safe Operation Area

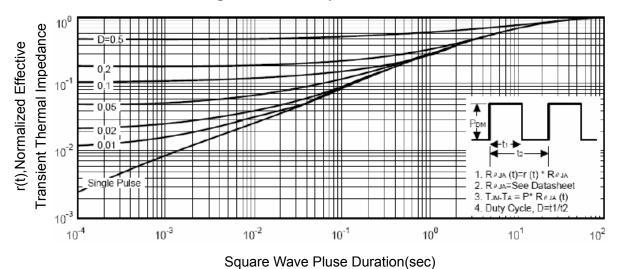
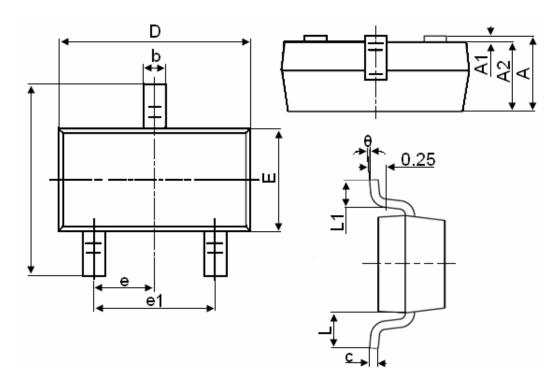


Figure 14 Normalized Maximum Transient Thermal Impedance



SOT-23 Package Information



| Symbol | | Dimensions in Millimeters | | |
|--------|-------|---------------------------|--|--|
| Symbol | MIN. | MAX. | | |
| Α | 0.900 | 1.150 | | |
| A1 | 0.000 | 0.100 | | |
| A2 | 0.900 | 1.050 | | |
| b | 0.300 | 0.500 | | |
| С | 0.080 | 0.150 | | |
| D | 2.800 | 3.000 | | |
| Е | 1.200 | 1.400 | | |
| E1 | 2.250 | 2.550 | | |
| е | | 0.950TYP | | |
| e1 | 1.800 | 2.000 | | |
| L | | 0.550REF | | |
| L1 | 0.300 | 0.500 | | |
| θ | 0° | 8° | | |

Notes

- 1. All dimensions are in millimeters.
- 2. Tolerance ± 0.10 mm (4 mil) unless otherwise specified
- 3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- 4. Dimension L is measured in gauge plane.
- 5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.



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